NSN 5962-01-413-4899

Memory Microcircuit - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5962-01-413-4899

Maximum Power Dissipation Rating:
1.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
F-16 acft
Features Provided:
Electrostatic sensitive and monolithic
Inclosure Material:
Silicon
Inclosure Configuration:
Leadless flat pack
Output Logic Form:
Complementary-metal oxide-semiconductor logic
Criticality Code Justification:
Cbbl
Terminal Surface Treatment:
Solder
Product Name:
Microcircuits, memory, digital, cmos 32k x 8 eeprom, monolithic silicon
Voltage Rating And Type Per Characteristic:
-0.3 volts total supply and 6.3 volts total supply
Time Rating Per Chacteristic:
70.00 nanoseconds af output megawatts
Memory Device Type:
Eeprom
Special Features:
10 ms write speed, byte/page write mode, data polling/toggle bit end ofwrite indicator, 10, 000 cycles endurance
Test Data Document:
96906-mil-std883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
32 leadless
Shelf Life:
N/a
Unit Of Measure:

Demilitarization:
No
Fiig:
A458a0